

EconoDUAL™ Modul mit Trench/Feldstop IGBT3 und High Efficiency Diode
EconoDUAL™ module with trench/fieldstop IGBT3 and Emitter Controlled High Efficiency diode

Vorläufige Daten
Preliminary Data

IGBT, Wechselrichter / IGBT, Inverter

Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
Kollektor-Dauergleichstrom Continuous DC collector current	$T_C = 80^{\circ}\text{C}, T_{vj\max} = 150^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\max} = 150^{\circ}\text{C}$	$I_{C\text{nom}}$ I_C	150 200	A A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	300	A
Gesamt-Verlustleistung Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 150$	P_{tot}	695	W
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 150\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 150\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,70 2,00	2,15	V V
Gate-Schwellenspannung Gate threshold voltage	$I_C = 6,00\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		$V_{G\text{Eth}}$	5,0	5,8	6,5 V
Gateladung Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G	1,40		μC
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		$R_{G\text{int}}$	1,3		Ω
Eingangskapazität Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	10,5		nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,50		nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		5,0	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		400	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 150\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{on}} = 8,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$t_{d\text{on}}$	0,25 0,30		μs μs
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 150\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{on}} = 8,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	t_r	0,09 0,10		μs μs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 150\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{off}} = 8,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$t_{d\text{off}}$	0,55 0,65		μs μs
Fallzeit, induktive Last Fall time, inductive load	$I_C = 150\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{off}} = 8,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	t_f	0,13 0,16		μs μs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 150\text{ A}, V_{CE} = 600\text{ V}, L_S = 80\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 2600\text{ A}/\mu\text{s}$ $R_{G\text{on}} = 8,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	E_{on}	8,00 11,0		mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 150\text{ A}, V_{CE} = 600\text{ V}, L_S = 80\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 3600\text{ V}/\mu\text{s}$ $R_{G\text{off}} = 8,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	E_{off}	16,0 24,0		mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 900\text{ V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 125^{\circ}\text{C}$		I_{SC}	600		A
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro IGBT / per IGBT		R_{thJC}		0,18	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,03		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{op}}$	-40	125	$^{\circ}\text{C}$

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**Vorläufige Daten
Preliminary Data**

Diode, Wechselrichter / Diode, Inverter

Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzensperrspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
Dauergleichstrom Continuous DC forward current		I_F	150	A
Periodischer Spitzenstrom Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	300	A
Grenzlastintegral I^2t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$	I^2t	4600	A^2s

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	$I_F = 150\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 150\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	V_F	1,65 1,65	2,15	V V
Rückstromspitze Peak reverse recovery current	$I_F = 150\text{ A}, -di_F/dt = 2600\text{ A}/\mu\text{s} (T_{vj}=125^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	I_{RM}	110 140		A A
Sperrverzögerungsladung Recovered charge	$I_F = 150\text{ A}, -di_F/dt = 2600\text{ A}/\mu\text{s} (T_{vj}=125^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	Q_r	15,0 28,0		μC μC
Abschaltenergie pro Puls Reverse recovery energy	$I_F = 150\text{ A}, -di_F/dt = 2600\text{ A}/\mu\text{s} (T_{vj}=125^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	E_{rec}	7,00 14,0		mJ mJ
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro Diode / per diode		R_{thJC}		0,34	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro Diode / per diode $\lambda_{paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,05		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{ op}}$	-40	125	$^{\circ}\text{C}$

NTC-Widerstand / NTC-Thermistor

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Nennwiderstand Rated resistance	$T_C = 25^{\circ}\text{C}$		R_{25}	5,00		k Ω
Abweichung von R100 Deviation of R100	$T_C = 100^{\circ}\text{C}, R_{100} = 493\ \Omega$		$\Delta R/R$	-5	5	%
Verlustleistung Power dissipation	$T_C = 25^{\circ}\text{C}$		P_{25}		20,0	mW
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$		$B_{25/50}$	3375		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$		$B_{25/80}$	3411		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$		$B_{25/100}$	3433		K

Angaben gemäß gültiger Application Note.
Specification according to the valid application note.

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**Vorläufige Daten
Preliminary Data**

Modul / Module

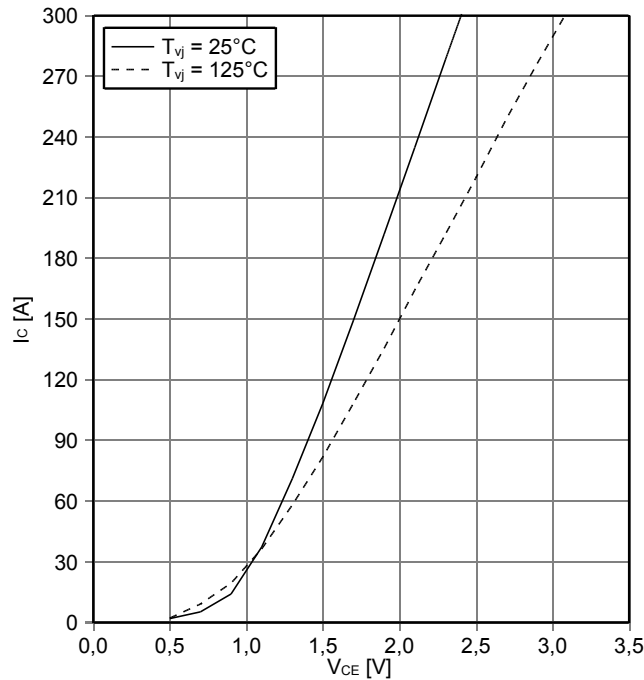
Isolations-Prüfspannung Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISOL}	2,5		kV
Material Modulgrundplatte Material of module baseplate			Cu		
Innere Isolation Internal isolation	Basisisolierung (Schutzklasse 1, EN61140) basic insulation (class 1, IEC 61140)		Al ₂ O ₃		
Kriechstrecke Creepage distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		14,5 13,0		mm
Luftstrecke Clearance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		12,5 10,0		mm
Vergleichszahl der Kriechwegbildung Comperative tracking index		CTI	> 225		
			min. typ. max.		
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro Modul / per module $\lambda_{\text{Paste}} = 1 \text{ W/(m}\cdot\text{K)} / \lambda_{\text{grease}} = 1 \text{ W/(m}\cdot\text{K)}$	R _{thCH}	0,009		K/W
Modulstreuinduktivität Stray inductance module		L _{sCE}	20		nH
Modulleitungswiderstand, Anschlüsse - Chip Module lead resistance, terminals - chip	T _c = 25°C, pro Schalter / per switch	R _{CC+EE'}	1,10		mΩ
Lagertemperatur Storage temperature		T _{stg}	-40	125	°C
Anzugsdrehmoment f. Modulmontage Mounting torque for modul mounting	Schraube M5 - Montage gem. gültiger Applikationsschrift Screw M5 - Mounting according to valid application note	M	3,00	-	6,00 Nm
Anzugsdrehmoment f. elektr. Anschlüsse Terminal connection torque	Schraube M6 - Montage gem. gültiger Applikationsschrift Screw M6 - Mounting according to valid application note	M	3,0	-	6,0 Nm
Gewicht Weight		G	345		g

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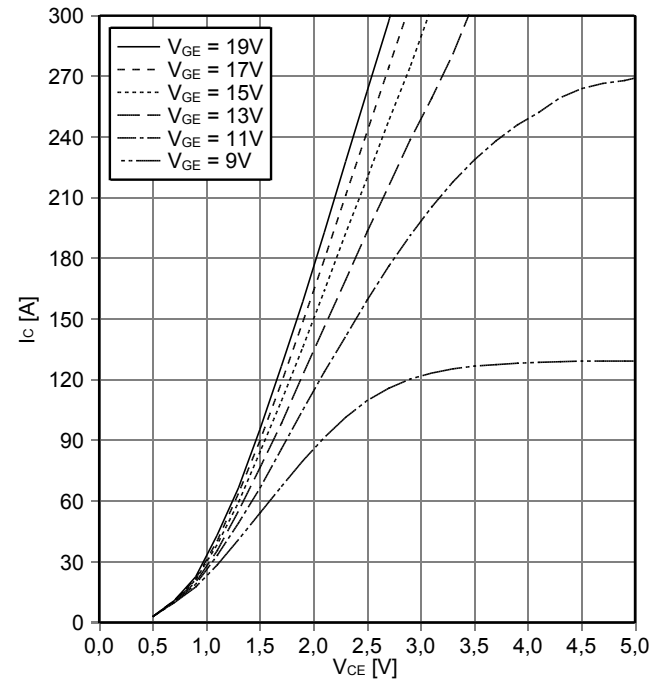
Ausgangskennlinie IGBT, Wechselrichter (typisch)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



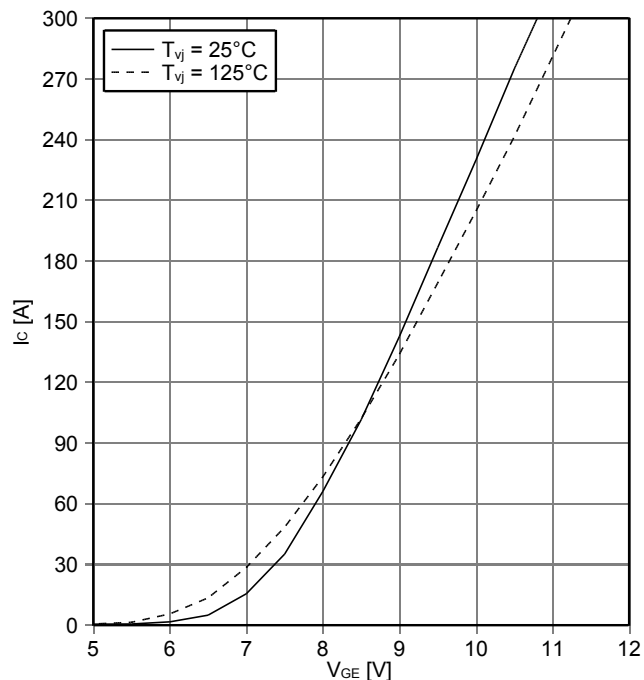
Ausgangskennlinienfeld IGBT, Wechselrichter (typisch)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 125^\circ\text{C}$



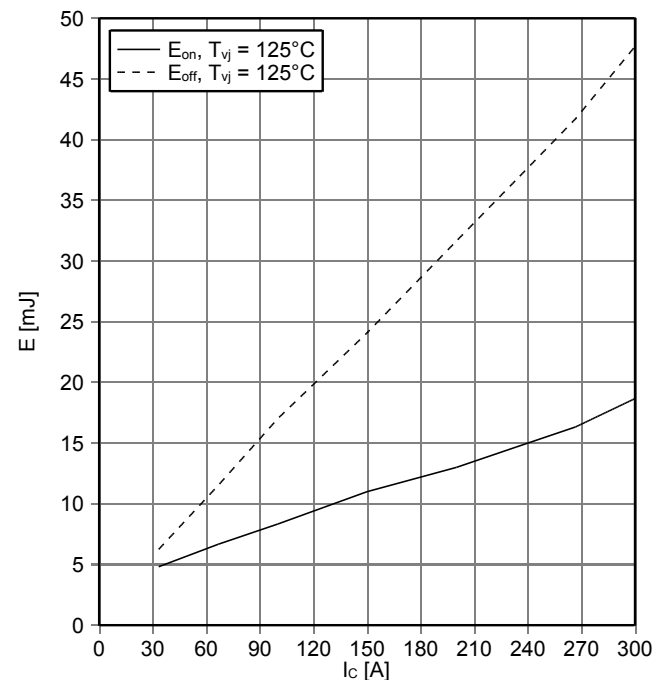
Übertragungscharakteristik IGBT, Wechselrichter (typisch)
transfer characteristic IGBT, Inverter (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



Schaltverlust IGBT, Wechselrichter (typisch)
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C), E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}, R_{Gon} = 8.2\ \Omega, R_{Goff} = 8.2\ \Omega, V_{CE} = 600\text{ V}$



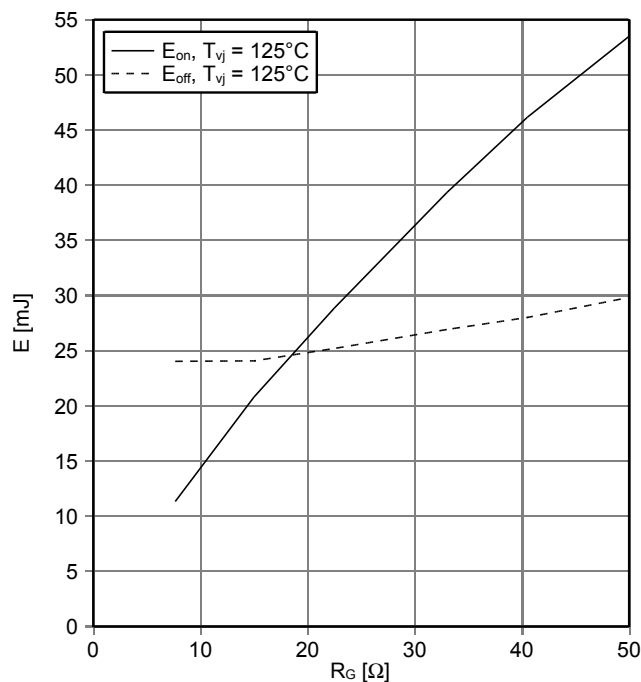
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Vorläufige Daten Preliminary Data

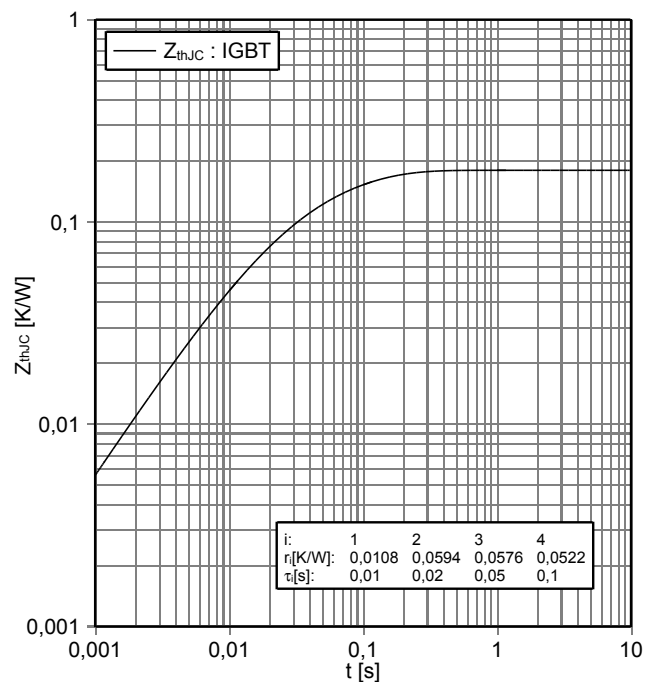
Schaltverluste IGBT, Wechselrichter (typisch) switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 150\text{ A}$, $V_{CE} = 600\text{ V}$



Transienter Wärmewiderstand IGBT, Wechselrichter transient thermal impedance IGBT, Inverter

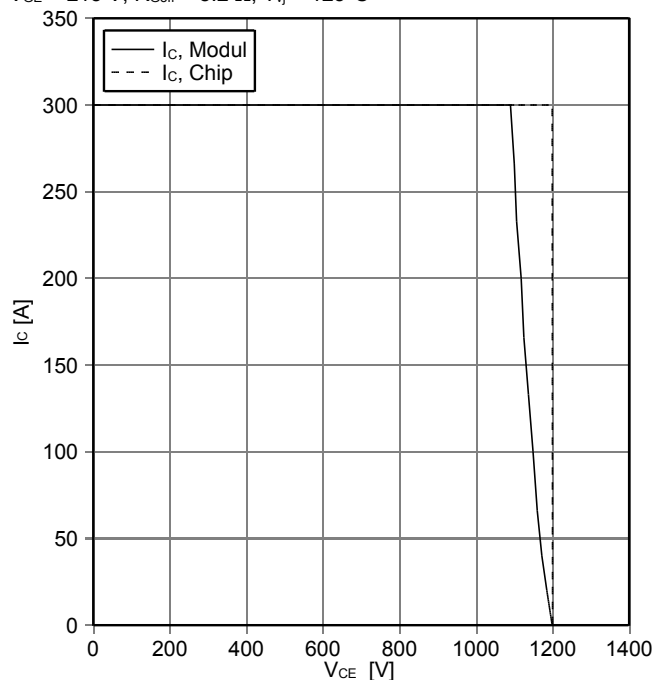
$Z_{thJC} = f(t)$



Sicherer Rückwärts-Arbeitsbereich IGBT, Wechselrichter (RBSOA)

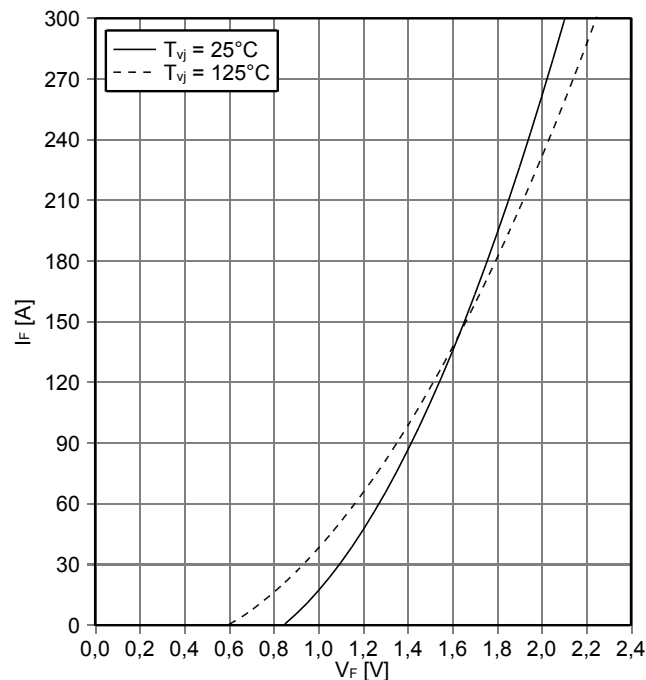
reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 8.2\ \Omega$, $T_{vj} = 125^\circ\text{C}$



Durchlasskennlinie der Diode, Wechselrichter (typisch) forward characteristic of Diode, Inverter (typical)

$I_F = f(V_F)$



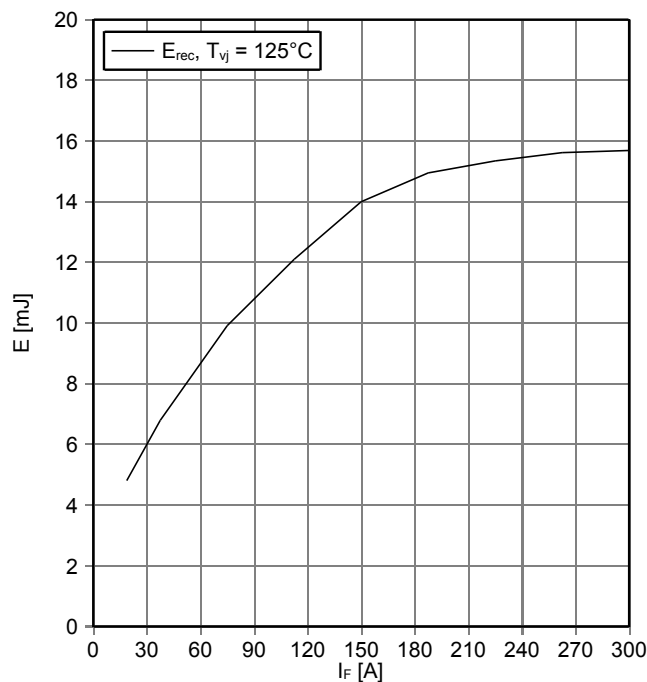
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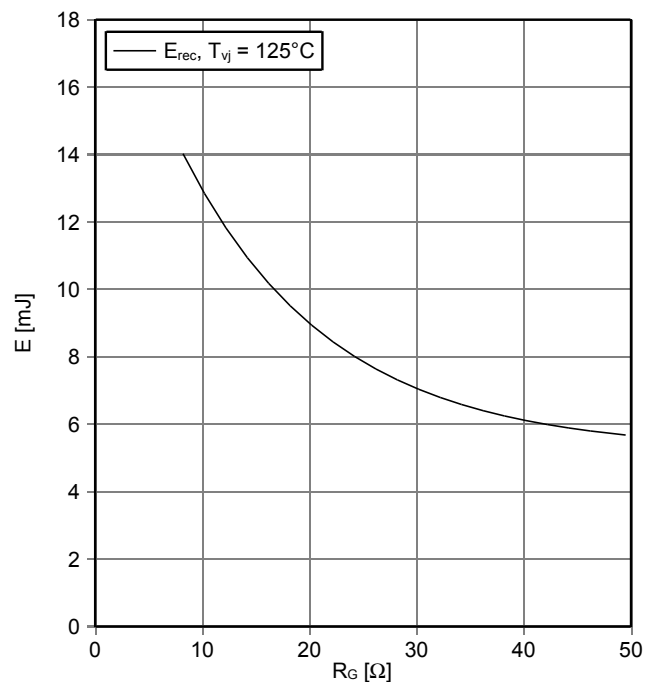
Schaltverluste Diode, Wechselrichter (typisch) switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 8.2 \Omega, V_{CE} = 600 V$



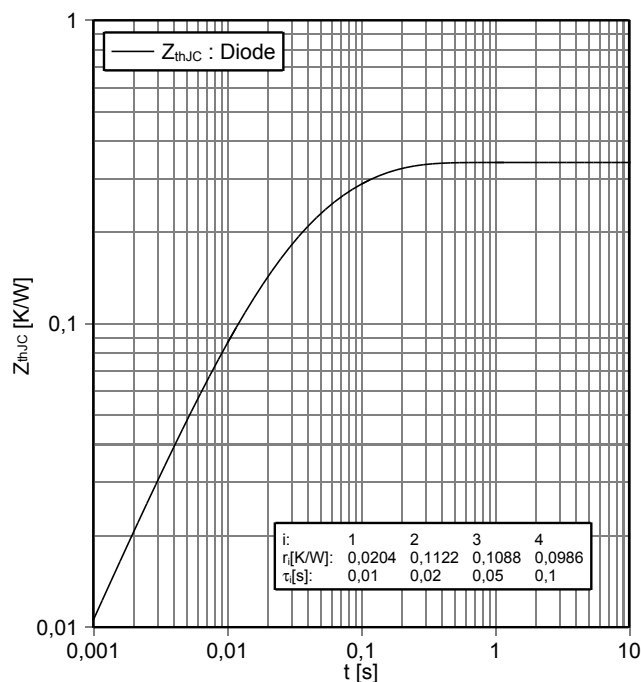
Schaltverluste Diode, Wechselrichter (typisch) switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$
 $I_F = 150 A, V_{CE} = 600 V$



Transienter Wärmewiderstand Diode, Wechselrichter transient thermal impedance Diode, Inverter

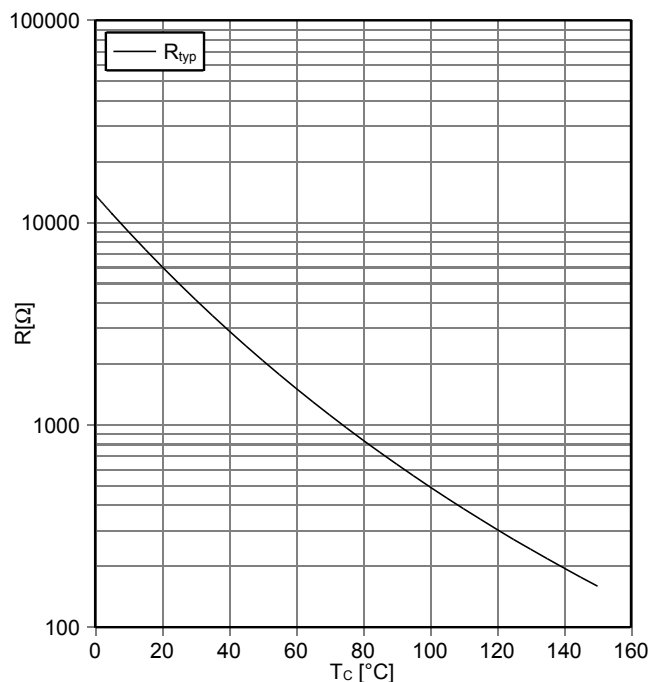
$Z_{thJC} = f(t)$



i:	1	2	3	4
r[K/W]:	0,0204	0,1122	0,1088	0,0986
τ[s]:	0,01	0,02	0,05	0,1

NTC-Widerstand-Temperaturkennlinie (typisch) NTC-Thermistor-temperature characteristic (typical)

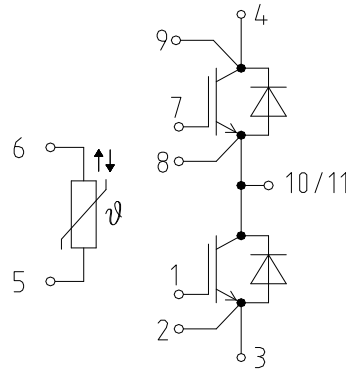
$R = f(T)$



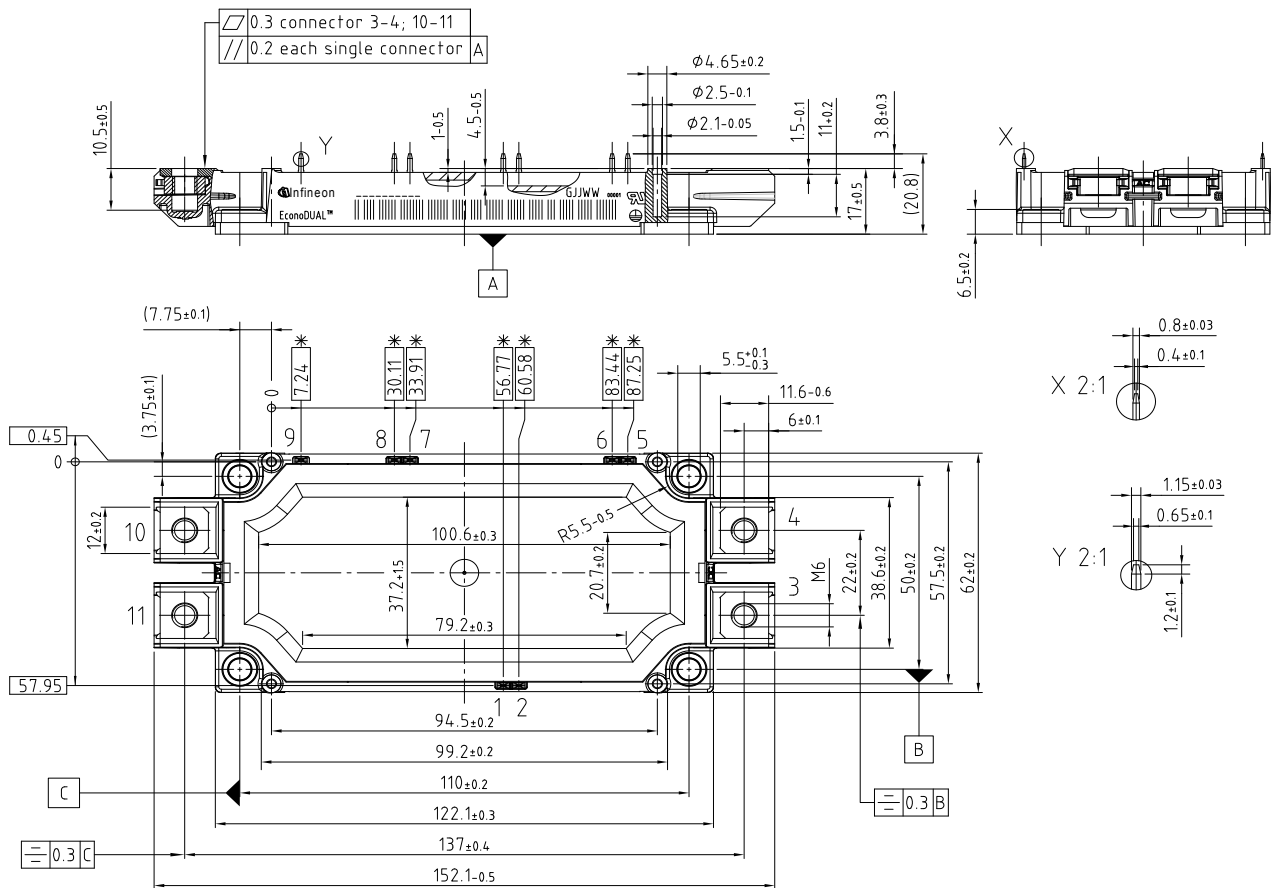
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Vorläufige Daten
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Schaltplan / circuit_diagram_headline



Gehäuseabmessungen / package outlines



* = all dimensions with a tolerance of ± 0.5
dimensions valid in mounted condition

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